#### NOT RECOMMENDED FOR NEW DESIGN **USE DSS4160V**





# DNLS160V

# LOW V<sub>CE(SAT)</sub> NPN SURFACE MOUNT TRANSISTOR

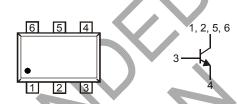
#### **Features**

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DPLS160V)
- Surface Mount Package Suited for Automated Assembly
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 1)
- "Green Device" (Note 2)
- Qualified to AEC-Q 101 Standards for High Reliability

# **Mechanical Data**

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.003 grams (approximate)





# Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current - Continuous	lc	1	Α
Peak Pulse Collector Current	I <sub>CM</sub>	2	Α
Base Current (DC)	I <sub>B</sub>	300	mA

#### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	$P_D$	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	$T_J$ , $T_{STG}$	-55 to +150	°C

Notes:

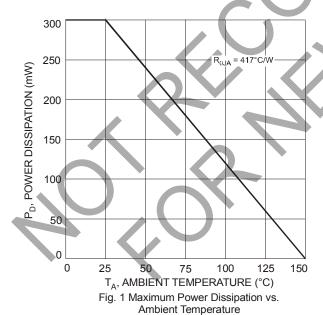
- No purposefully added lead.
- Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document P02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

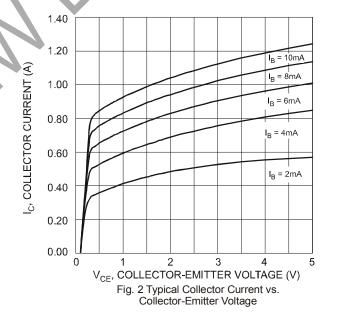


### Electrical Characteristics @TA = 25°C unless otherwise specified

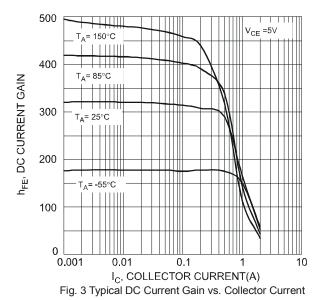
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	60		_	V	$I_{C} = 10 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current				100	nA	$V_{CB} = 60V, I_{E} = 0$
Collector Cutoff Current	I <sub>CBO</sub>			50	μΑ	$V_{CB} = 60V, I_{E} = 0, T_{A} = 150^{\circ}C$
Collector Cutoff Current	I <sub>CES</sub>			100	nA	$V_{CE} = 60V, V_{BE} = 0$
Emitter Cutoff Current	I <sub>EBO</sub>			100	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
		250	320	_		$V_{CE} = 5V$ , $I_C = 1mA$
DC Current Gain	$h_{FE}$	200	280	_	V	$V_{CE} = 5V, I_{C} = 500 \text{mA}$
		100	165	_		$V_{CE} = 5V$ , $I_C = 1A$
		_	80	110	_ `	$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	_	80	140	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	140	250		$I_C = 1A$ , $I_B = 100mA$
Collector-Emitter Saturation Resistance	R <sub>CE(SAT)</sub>	_	140	250	mΩ	$I_C = 1A$ , $I_B = 100mA$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$		0.91	1.1	V	$I_C = 1A$ , $I_B = 50mA$
Base-Emitter Turn On Voltage	V <sub>BE(ON)</sub>		0.81	0.9	V	$V_{CE} = 5V, I_{C} = 1A$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	$C_{obo}$	_	7	10	pF	$V_{CB} = 10V, f = 1.0MHz$
Current Gain-Bandwidth Product	$f_T$	150 🕢	270		MHz 🍓	$V_{CE} = 10V$ , $I_{C} = 50mA$ , $f = 100MHz$
SWITCHING CHARACTERISTICS						
Turn-On Time	t <sub>on</sub>		90	_	ns	
Delay Time	t <sub>d</sub>	A A	17		ns	
Rise Time	t <sub>r</sub>		73		ns	V <sub>CC</sub> = 10V
Turn-Off Time	t <sub>off</sub>		300		ns	$I_C = 0.5A$ , $I_{B1} = I_{B2} = 25mA$
Storage Time	ts	P. L.	220	~	ns	
Fall Time	tí		80	-	ns	

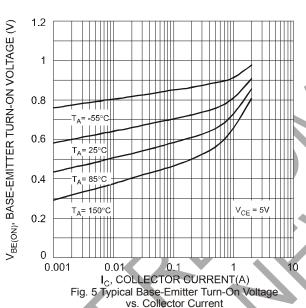
Notes: 4. Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ .

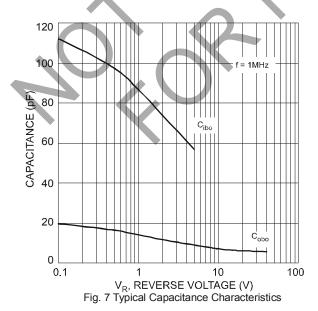












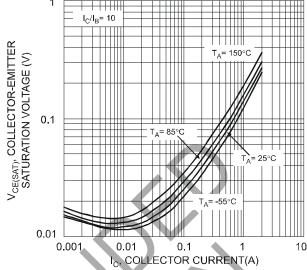


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

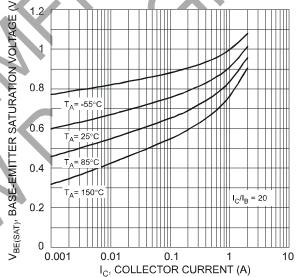
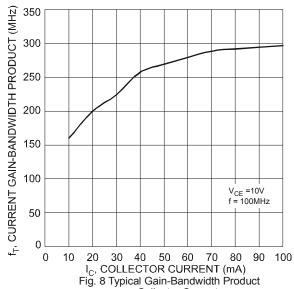


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



vs. Collector Current

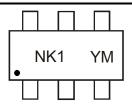


#### **Ordering Information** (Note 5)

Device	Packaging	Shipping
DNLS160V-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**

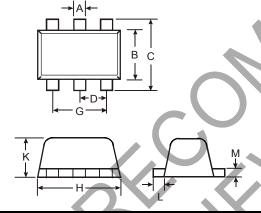


NK1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: V = 2008 M = Month ex: 9 = September

Date Code Key

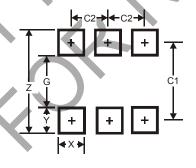
Year	2008		2009	2010	)	2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
							-					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	a	0	N	D

# **Package Outline Dimensions**



	207	F F00					
	SOT-563						
Dim	Min	Max	Typ				
A	0.15	0.30	0.20				
В	1.10	1.25	1.20				
O	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All	All Dimensions in mm						

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5
·	

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